

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	658	324/760.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 08:24
L2	1818	716/4.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 08:24
L3	3	((I1 I2) and (burnin "burn-in" burn\$in) and ((quiescent iddq) adj (current (current adj density)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/13 08:25
S1	5	harris-george.in.	US-PGPUB; USPAT	OR	OFF	2005/07/11 08:46
S2	2	brown-randy.in.	US-PGPUB; USPAT	OR	OFF	2005/07/11 08:25
S3	0	S1 and S2	US-PGPUB; USPAT	OR	OFF	2005/07/13 08:23
S4	0	((quiescent adj current) iddq) and ("burn-in" (burn adj in)) and ((reference baseline threshold) near3 temperature) and ((reference baseline threshold) near3 (current adj density))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 08:53
S5	72	((quiescent adj current) iddq) and ("burn-in" (burn adj in))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 08:54
S6	2	((quiescent adj current) iddq) and ("burn-in" (burn adj in)) and ((reference baseline threshold) adj (temperature (current adj density)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 08:53
S7	0	((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density))) and ((recorded logged documented existing) with (burn\$in adj (information data))) and ((hypothetical theoretical probable) ((quiescent adj current) iddq)) and (ratio with (hypothetical theoretical probable) with (reference base\$line threshold standard) with ((quiescent adj current) iddq)) and (((hypothetical theoretical probable) near3 process near3 (parameter metric)) with (reference base\$line threshold standard)) and (temperature with based with ratio with (reference base\$line threshold standard) near3 ((quiescent adj current) iddq)) and (measur\$4 near3 process near3 (parameter metric)) and (compari\$3 with (hypothetical theoretical probable) near3 process near3 (parameter metric)) and (determin\$5 with (actual real) with (bum\$in near3 temperature)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:09
S8	62840	((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:09

S9	0	((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density))) and ((hypothetical theoretical probable) ((quiescent adj current) iddq)) and (ratio with (hypothetical theoretical probable) with (reference base\$line threshold standard) with ((quiescent adj current) iddq)) and (((hypothetical theoretical probable) near3 process near3 (parameter metric)) with (reference base\$line threshold standard)) and (temperature with based with ratio with (reference base\$line threshold standard) near3 ((quiescent adj current) iddq)) and (measur\$4 near3 process near3 (parameter metric)) and (compari\$3 with (hypothetical theoretical probable) near3 process near3 (parameter metric)) and (determin\$5 with (actual real) with (bum\$in near3 temperature)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:12
S10	7184	((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density))) and ((hypothetical theoretical probable) ((quiescent adj current) iddq))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:10
S11	177	((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density))) and (measur\$4 near3 process near3 (parameter metric))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:16
S12	0	(predict\$3 with (burn\$in near3 (temperature condition state status)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:36
S13	1799	((burn\$in near3 (temperature condition state status)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:15
S14	0	S13 and ((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density))) and (measur\$4 near3 process near3 (parameter metric))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:15
S15	10	((semiconductor wafer die chip) with manufactur\$3) and ((reference base\$line threshold standard) near3 ((quiescent adj current) iddq temperature (current adj density))) and (measur\$4 near3 process near3 (parameter metric))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:20
S16	5	((semiconductor wafer die chip) with manufactur\$3) and ((reference base\$line threshold standard) near3 ((quiescent adj current) iddq)) and burn\$in	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:25
S17	2	texas adj instrument adj incorporated.as. and ((semiconductor wafer die chip) with manufactur\$3) and ((reference base\$line threshold standard) near3 ((quiescent adj current) iddq)) and burn\$in	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:25

S18	2	texas adj instrument adj incorporated.as. and ((reference base\$line threshold standard) near3 ((quiescent adj current) iddq)) and burn\$in	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:26
S19	216	texas adj instrument adj incorporated.as. and burn\$in	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 12:13
S20	0	texas adj instrument adj incorporated.as. and (predict\$3 with burn\$in with (condition state status))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:30
S21	47	texas adj instrument adj incorporated.as. and (burn\$in with (condition state status))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:27
S22	2	texas adj instrument adj incorporated.as. and (burn\$in with (condition state status)) and ((quiescent adj current) iddq)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 09:28
S23	195	324/71.5.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:28
S24	274	324/719.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:28
S25	1860	438/14.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S26	941	438/17.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S27	172	702/31.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S28	426	702/57.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S29	439	702/64.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S30	324	702/65.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S31	301	702/81.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S32	97	702/83.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S33	302	702/84.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S34	318	702/127.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:29
S35	469	702/179.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:30
S36	309	702/181.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:30
S37	957	702/182.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:30
S38	607	702/189.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/11 09:30

S39	6	((S23 S24 S25 S26 S27 S28 S29 S30 S31 S32 S33 S34 S35 S36 S37 S38) and burn\$in and ((quiescent adj current) iddq)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/13 07:57
S40	9	(predict\$3 same (burn\$in near3 ((quiescent adj current) iddq temperature condition state status)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 10:09
S41	3	((semiconductor wafer die chip) with manufactur\$3) and predict\$3 and burn\$in and ((quiescent adj current) iddq)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 09:43
S42	24	((predict\$3 model\$3) same (burn\$in near3 ((quiescent adj current) iddq temperature condition state status)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 10:11
S43	5	((predict\$3 model\$3) with (burn\$in near3 ((quiescent adj current) iddq temperature condition state status)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 10:10
S44	0	((predict\$3 model\$3) same (burn\$in near3 ((quiescent adj current) iddq temperature condition state status))) and ((quiescent adj current) iddq)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 10:11
S45	5	(predict\$3 model\$3) and (burn\$in near3 ((quiescent adj current) iddq temperature condition state status)) and ((quiescent adj current) iddq)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 11:05
S46	2	((semiconductor wafer die ic (integrated adj circuit) (logic adj circuit)) near3 (manufactur\$3 produc\$4)) and ((predict\$3 model\$3) same burn\$in) and ((quiescent adj current) iddq)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 11:10
S47	68	("5539652").URPN.	USPAT	OR	OFF	2005/07/11 11:14
S48	2	("5539652").URPN. and (burn\$in burnin)	USPAT	OR	ON	2005/07/11 11:14
S49	3	("5635850").URPN.	USPAT	OR	OFF	2005/07/11 11:16
S50	1	("5635850").URPN. and (burn\$in burnin)	USPAT	OR	ON	2005/07/11 11:17
S51	0	(S46 S47 S48 S49 S50) and ((predict\$3 forecast\$3 project\$3) same ((burn\$in burnin) with (condition state status result outcome)))	USPAT	OR	ON	2005/07/11 11:19

S52	158	((predict\$3 forecast\$3 project\$3) same ((burn\$in burnin) with (condition state status result outcome)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 11:21
S53	6	((predict\$3 forecast\$3 project\$3) same ((burn\$in burnin) with (condition state status result outcome)))	EPO; JPO; DERWENT	OR	ON	2005/07/11 11:20
S54	0	((predict\$3 forecast\$3 project\$3) same ((burn\$in burnin) with (condition state status result outcome)))	IBM_TDB	OR	ON	2005/07/11 12:14
S55	50	((semiconductor wafer die chip ic ((integrated logic) adj (circuit component module part section))) with (manufactur\$3 produc\$4 test\$3)) and ((predict\$3 forecast\$3 project\$3) same ((burn\$in burnin) with (condition state status result outcome)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 11:27
S56	13	((semiconductor wafer die chip ic ((integrated logic) adj (circuit component module part section))) with (manufactur\$3 produc\$4 test\$3)) and ((predict\$3 forecast\$3 project\$3) with (burn\$in burnin) with (condition state status result outcome))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 11:28
S57	26	hewlett adj packard.as. and burn\$in	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/11 12:13
S58	1	((texas adj instrument) (hewlett adj packard) intel motorola rca (radio adj corpoartion adj america)).as. and ((predict\$3 forecast\$3 project\$3) with ((burn\$in burnin) with (condition state status result outcome)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 12:36
S59	0	infineon adj technolog\$.as. and ((predict\$3 forecast\$3 project\$3) with ((burn\$in burnin) with (condition state status result outcome)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 12:38
S60	17910	infineon adj technolog\$.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 12:38
S61	24	infineon adj technolog\$.as. and ((burn\$in burnin) with (condition state status result outcome))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 12:42
S62	0	(S1 S2) and (burn\$in burnin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/11 13:18

S63	97	(burnin burn\$in "burn-in") and ((base\$line reference gold golden standard threshold set\$point) adj (temperature iddq (quiescent adj (current (current adj density))))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:51
S64	0	((set\$point reference standard baseline) near3 (process adj (parameter variable data metric))) and ((set\$point reference standard baseline) near3 ((burnin "burn-in" bum-in) adj temperature)) and ((set\$point reference standard baseline) near3 ((burnin "burn-in" bum-in) adj voltage)) and ((set\$point reference standard baseline) near3 ((iddq quiescent) adj (current (current adj density)))) and theoretical and ratio	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/07/12 08:13
S65	0	(process adj (parameter variable data metric)) and ((burnin "burn-in" bum-in) adj temperature) and ((burnin "burn-in" bum-in) adj voltage) and ((iddq quiescent) adj (current (current adj density))) and theoretical and ratio and (difference differential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:15
S66	0	(process adj (parameter variable data metric)) and ((burnin "burn-in" bum-in) adj (temperature voltage ((iddq quiescent) adj (current (current adj density)))))) and theoretical and ratio and (difference differential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:16
S67	3	(process adj (parameter variable data metric)) and ((burnin "burn-in" bum-in) adj (temperature voltage ((iddq quiescent) adj (current (current adj density)))))) and ratio and (difference differential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:25
S68	527	(burnin "burn-in" bum-in) and ((plot plotting graph graphing) with (temperature voltage ((iddq quiescent) adj (current (current adj density))))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:26
S69	0	(burnin "burn-in" bum-in) and ((plot plotting graph graphing) with temperature) and ((plot plotting graph graphing) with voltage) and ((iddq quiescent) adj (current (current adj density)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:27
S70	25	(burnin "burn-in" bum-in) and ((plot plotting graph graphing) with temperature) and ((plot plotting graph graphing) with voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:28

S71	818	((burnin burn\$in "burn-in") with (oven compartment enclosure))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:52
S72	291	((semiconductor wafer chip die ic ((integrated logic) adj (circuit gate))) near3 (manufacture manufacturing producing production)) and ((burnin burn\$in "burn-in") with (oven compartment enclosure))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:58
S73	2	((semiconductor wafer chip die ic ((integrated logic) adj (circuit gate))) near3 (manufacture manufacturing producing production)) and ((burnin burn\$in "burn-in") with (oven compartment enclosure)) and ((iddq quiescent) adj (current (current adj density)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:56
S74	74	((semiconductor wafer chip die ic ((integrated logic) adj (circuit gate))) near3 (manufacture manufacturing producing production)) and ((burnin burn\$in "burn-in") with (oven compartment enclosure)) and temperature and voltage and (metric variable parameter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 08:59
S75	38	((semiconductor wafer chip die ic ((integrated logic) adj (circuit gate))) near3 (manufacture manufacturing producing production)) and ((burnin burn\$in "burn-in") with (oven compartment enclosure)) and temperature and voltage and (metric variable parameter) and (predict predicted predicting prediction project projected projecting projection forecast forecasted forecasting) and (reference standard base\$line threshold set\$point target)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/12 09:19
S76	0	((semiconductor wafer chip die ic ((integrated logic) adj (circuit gate))) near3 (manufacture manufacturing producing production)) and ((predict predicted predicting prediction project projected projecting projection forecast forecasted forecasting) with (burnin burn\$in "burn-in") with (condition state status result outcome)) and ((burnin burn\$in "burn-in") adj temperature) and ((burnin burn\$in "burn-in") adj voltage)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 09:22
S77	5	((semiconductor wafer chip die ic ((integrated logic) adj (circuit gate))) near3 (manufacture manufacturing producing production)) and ((predict predicted predicting prediction forecast forecasted forecasting) with (burnin burn\$in "burn-in") with (condition state status result outcome))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:06

S78	478	iddq	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:06
S79	20	((baseline reference standard set\$point threshold minimum) adj iddq	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:09
S80	0	((baseline reference standard set\$point threshold minimum) adj iddq) and ((baseline reference standard set\$point threshold minimum) adj temperature)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:10
S81	56	((baseline reference standard set\$point threshold minimum) adj ((iddq quiescent) adj (current (current adj density))))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:26
S82	0	((baseline reference standard set\$point threshold minimum) adj ((iddq quiescent) adj (current (current adj density)))) and ((baseline reference standard set\$point threshold minimum) adj temperature)	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:12
S83	0	((baseline reference standard set\$point threshold minimum) adj ((iddq quiescent) adj (current (current adj density)))) and ((theorized theoretal probabalistic probability probable ideal idealized expected) adj ((iddq quiescent) adj (current (current adj density))))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:14
S84	2	((baseline reference standard set\$point threshold minimum) adj ((iddq quiescent) adj (current (current adj density)))) and ((theorized theoretal probabalistic probability probable ideal idealized expected) with ((iddq quiescent) adj (current (current adj density))))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 13:14
S85	3	(burnin "burn-in" (burn adj in)) and ((baseline reference standard set\$point threshold minimum) adj ((iddq quiescent) adj (current (current adj density))))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/12 14:47
S86	4	("6377897" "6175812" "6326800" "6215324").pn.	USPAT	OR	OFF	2005/07/12 14:58
S87	0	("6377897" "6175812" "6326800" "6215324").pn. and (compari\$3 with (actual real measured) with (ideal idealized theoretal) with metric) and ((real actual measured) with ((burnin "burn-in" (bum adj in)) near3 temperature))	USPAT	OR	ON	2005/07/12 14:52
S88	0	("6377897" "6175812" "6326800" "6215324").pn. and ((difference differential) with (actual real measured) with (ideal idealized theoretal) with metric) and ((change changing alter alteration altered changed altering adjustment adjust adjusted adjusting) with ((reference threshold set\$point baseline) near3 temperature))	USPAT	OR	ON	2005/07/12 14:55

S89	0	("6377897" "6175812" "6326800" "6215324").pn. and ((difference differential) with (actual real measured) with (ideal idealized theoretical) with metric) and ((change changing alter alteration altered changed altering adjustment adjust adjusted adjusting) with ((reference threshold set\$point baseline) near3 temperature)) and (((("10" ten) ("15" fifteen)) with (centigrade celsius) with (difference differential) with (greater larger exceed more) with ("100" (one adj hundred))))	USPAT	OR	ON	2005/07/12 14:58
S90	516	702/130.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:56
S91	195	324/71.5.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S92	274	324/719.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S93	1862	438/14.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S94	942	438/17.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S95	173	702/31.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S96	427	702/57.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S97	439	702/64.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S98	324	702/65.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S99	301	702/81.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S100	97	702/83.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S101	302	702/84.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S102	318	702/127.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S103	471	702/179.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S104	309	702/181.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S105	959	702/182.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S106	610	702/189.ccls.	US-PGPUB; USPAT	OR	OFF	2005/07/13 07:58
S107	4	(S90 S91 S92 S93 S94 S95 S96 S97 S98 S99 S100 S101 S102 S103 S104 S105 S106) and (burnin "burn-in" burn\$in) and ((quiescent iddq) adj (current (current adj density)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/13 08:24